

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
SETI-0005	
Applicant(s) Gaska et al.	

Filing Date	Group Art Unit
Herewith	

*EXAMINER INITIAL	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
	"Introduction to Solid State Lighting," A. Zukausas et al., John Wiley & Sons, Inc., New York (2002), pp. 37-116.
	"Improved Characteristics of InGaN Multiple-Quantum-Well Light-Emitting Diode by GaN/AlGaN Distributed Bragg Reflector Grown on Sapphire," N. Nakada et al., Applied Physics Letters, Vol. 76, No. 14, April 3, 2000, pp. 1804-1806.
	"AlGaN Single-Quantum-Well Light Emitting Diodes With Emission at 285 nm," V. Adivarahan et al., Applied Physics Letters, Vol. 81, No. 19, November 4, 2002, pp. 3666-3668.
	"Strain Energy Band Engineering Approach to AlN/GaN/InN Heterojunction Devices," A. Khan et al., Frontiers in Electronics: Future Chips Proceedings of the 2002 Workshop on Frontiers in Electronics (Wofe-02) St. Croix, Virgin Islands, World Scientific Pub Co; (January 15, 2003), ISBN: 9812382224, Vol. 26. Series Selected Topics in Electronics and Systems, pp. 195-214.
	"A Vertical Injection Blue Light Emitting Diode in Substrate Separated InGaN Heterostructures," Y. -K. Song et al., Applied Physics Letters, Vol. 74, no. 24, June 14, 1999, pp. 3720-3722.
EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.